

IN THE CLAIMS:

Amend claim 8 and cancel claims 1-7 and 9-11 without prejudice or disclaimer as shown in the following listing of claims, which replaces all previous listings and versions of claims.

1.-7. (canceled)

8. (currently amended) A method of making a lamina sample by forming a lamina part by etching-working by scan-irradiating a focused ion beam to a sample surface, and taking out the lamina part, ~~characterized by~~ the method comprising:

a ~~1st~~ first process of sputtering-etching-working a 1st worked region for exposing a 1st side wall of a region, which is to be made a lamina, under a 1st focused ion beam condition of a 1st focused ion beam and, at the same time, sputtering-etching-working a 2nd worked region for exposing a 2nd side wall of the region, which is to be made the lamina, under a 1st focused ion beam condition of a 2nd focused ion beam,

a ~~2nd~~ second process of sputtering-etching-working the 2nd worked region under the 1st focused ion beam condition of the 1st focused ion beam and, at the same time,

sputtering-etching-working the 1st worked region ~~under-a~~ under  
a 1st focused ion beam condition of the 2nd focused ion beam,

a ~~3rd~~ third process of microscope-observing a  
surface portion of the lamina by scan-irradiating under a 3rd  
focused ion beam condition of the 2nd focused ion beam at the  
same time as sputtering-etching-working the 1st side wall by  
slanting the sample such that the 1st focused ion beam enters  
so as to correct, in the 1st side wall, its slant under a 2nd  
focused ion beam condition in which an acceleration voltage is  
low and/or a beam current is low ~~than~~ relative to the 1st  
focused ion beam condition by using the 1st focused ion beam,  
or with an irradiation of the 1st focused ion beam being  
temporarily interrupted, and finishing the etching working by  
the 1st focused ion beam by confirming the fact that a  
thickness of the lamina has become a 1st predetermined  
thickness by measuring the thickness of the lamina, and

a ~~4th~~ fourth process of microscope-observing the  
surface portion of the lamina by scan-irradiating under the  
3rd focused ion beam condition of the 2nd focused ion beam at  
the same time as sputtering-etching-working the 2nd side wall  
by slanting the sample such that the 1st focused ion beam  
enters so as to correct, in the 2nd side wall, its slant under  
the 2nd focused ion beam condition of the 1st focused ion  
beam, or with the irradiation of the 1st focused ion beam  
being temporarily interrupted, and finishing the etching

working by the 1st focused ion beam by confirming the fact that the ~~thickness~~ thickness of the lamina has become a 2nd predetermined thickness thinner than the 1st predetermined thickness by measuring the thickness of the lamina.

9.-11. (canceled)